

PATENT  
1781-0247P

## IN THE U.S. PATENT AND TRADEMARK OFFICE

*fee only*

Applicant: Soo Jin CHUA et al. Conf.: 5461  
Appl. No.: 10/633,652 Group: 2812  
Filed: August 5, 2003 Examiner: MULPURI, S.  
For: FORMING INDIUM NITRIDE (INN) AND INDIUM  
GALLIUM NITRIDE (INGAN) QUANTUM DOTS  
GROWN BY METAL-ORGANIC-VAPOR-PHASE-  
EPITAXY (MOCVD)

TERMINAL DISCLAIMER TRANSMITTAL

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

June 25, 2004

Sir:

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Please charge Deposit Account No. 02-2448 in the amount of \$110.00. This form is submitted in triplicate.

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M. U. Armstrong

Signature

M. U. ARMSTRONG

Typed or printed name of person signing certificate

Respectfully submitted,

BIRCH, STEWART, KOLASCH &amp; BIRCH, LLP

By Mark J. Nuell

Mark J. Nuell, #36,623

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(703) 205-8000

DRN/mua.  
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Attachment(s)

(Rev. 02/13/2004)

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Sir:

The National University of Singapore and Institute of  
Materials Research & Engineering, (hereinafter "the Assignees")

- ☐ residing at ,
- ☒ a university having an address of 10 Kent Ridge  
Crescent, 119260 Singapore, and
- ☒ a corporation of Singapore having a principal place of  
business at 3 Research Link, 117602 Singapore,  
respectively,

represent that it is the true owner of the entire interest of  
U.S. patent Application No. 6,645,885, filed on September 27,  
2001, for "FORMING INDIUM NITRIDE (INN) AND INDIUM GALLIUM  
NITRIDE (INGAN) QUANTUM DOTS GROWN BY METAL-ORGANIC-VAPOR-PHASE-  
EPITAXY (MOCVD)," (hereinafter "above-identified application") by  
virtue of and as evidenced by an Assignment recorded at the

Appl. No. 10/633,652

United States Patent and Trademark Office at Reel 12629, Frame(s)  
0655-0658.

The Assignees hereby disclaim the terminal part of any patent granted on the above-identified application which would extend beyond the expiration date of the full statutory term as presently shortened by any terminal disclaimer of U.S. Patent 6,645,885, and hereby agree that any patent so granted on the above-identified application shall be enforceable only for and during such period that the legal title to U.S. Patent 6,645,885 shall be the same as the legal title to any patent issuing from the above-identified application, this agreement to run with any patent granted on the above-identified application, and to be binding upon the grantee, its successors or assigns.

The Assignees do not disclaim any terminal part of any patent granted on the above-identified application prior to the expiration date of the full statutory term as presently shortened by any terminal disclaimer of U.S. Patent 6,645,885 in the event that it later expires for failure to pay a maintenance fee, is held unenforceable, is found invalid, is statutorily disclaimed in whole or terminally disclaimed under 37 C.F.R. § 1.321(a), has all claims canceled by a reexamination certificate, or is otherwise terminated prior to the expiration of its statutory term as presently shortened by any terminal disclaimer, except for the separation of legal title stated above.

This Terminal Disclaimer is submitted on behalf of the Assignees by the undersigned, an attorney of record in the above-identified application.

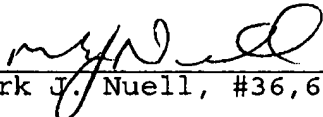
Appl. No. 10/633,652

Please charge any fees or credit any overpayment pursuant to  
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Respectfully submitted,

BIRCH, STEWART, KOLASCH & BIRCH, LLP

Date: June 25, 2004


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